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MCT2M, MCT2EM, MCT210M, MCT271M Phototransistor Optocouplers

Features

- UL recognized (File # E90700, Vol. 2)
- IEC60747-5-2 recognized (File # 102497)
 - Add option V (e.g., MCT2VM)

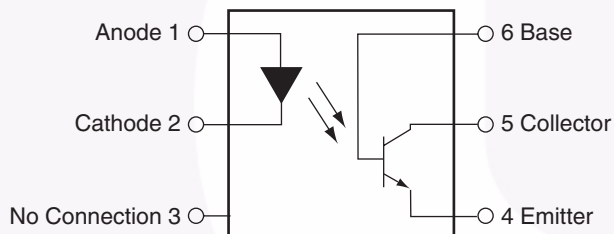
Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

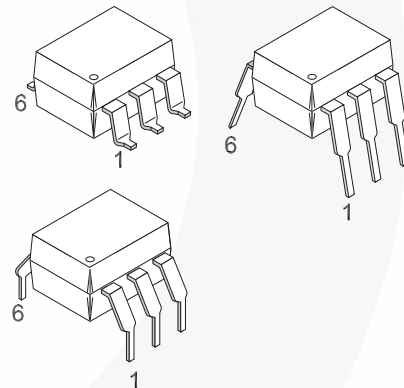
Description

The MCT2XXM series optoisolators consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line package.

Schematic



Package Outlines



Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Units
TOTAL DEVICE			
T_{STG}	Storage Temperature	-40 to +150	°C
T_{OPR}	Operating Temperature	-40 to +100	°C
T_{SOL}	Lead Solder Temperature	260 for 10 sec	°C
P_D	Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	250	mW
		2.94	mW/°C
EMITTER			
I_F	DC/Average Forward Input Current	60	mA
V_R	Reverse Input Voltage	3	V
$I_F(\text{pk})$	Forward Current – Peak (300 μs , 2% Duty Cycle)	3	A
P_D	LED Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	120	mW
		1.41	mW/°C
DETECTOR			
I_C	Collector Current	50	mA
V_{CEO}	Collector-Emitter Voltage	30	V
P_D	Detector Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	150	mW
		1.76	mW/°C

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)**Individual Component Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Typ.*	Max.	Units
EMITTER							
V_F	Input Forward Voltage	$I_F = 20\text{mA}$	MCT2M MCT2EM MCT271M		1.25	1.50	V
		$T_A = 0^\circ\text{C} - 70^\circ\text{C}$, $I_F = 40\text{mA}$	MCT210M		1.33		
I_R	Reverse Leakage Current	$V_R = 3.0\text{V}$	MCT2M MCT2EM MCT271M		0.001	10	μA
		$T_A = 0^\circ\text{C} - 70^\circ\text{C}$, $V_R = 6.0\text{V}$	MCT210M				
DETECTOR							
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 1.0\text{mA}$, $I_F = 0$	ALL	30	100		V
		$T_A = 0^\circ\text{C} - 70^\circ\text{C}$	MCT210M				
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}$, $I_F = 0$	MCT2M MCT2EM MCT271M	70	120		V
		$T_A = 0^\circ\text{C} - 70^\circ\text{C}$	MCT210M	30			
BV_{ECO}	Emitter-Collector Breakdown Voltage	$I_E = 100\mu\text{A}$, $I_F = 0$	MCT2M MCT2EM MCT271M	7	10		V
		$T_A = 0^\circ\text{C} - 70^\circ\text{C}$	MCT210M	6	10		
I_{CEO}	Collector-Emitter Dark Current	$V_{CE} = 10\text{V}$, $I_F = 0$	ALL		1	50	nA
		$V_{CE} = 5\text{V}$, $T_A = 0^\circ\text{C} - 70^\circ\text{C}$				30	μA
I_{CBO}	Collector-Base Dark Current	$V_{CB} = 10\text{V}$, $I_F = 0$	ALL			20	nA
C_{CE}	Capacitance	$V_{CE} = 0\text{V}$, $f = 1\text{MHz}$	ALL		8		pF

*All typical $T_A = 25^\circ\text{C}$ **Isolation Characteristics**

Symbol	Parameter	Test Conditions	Min	Typ*	Max	Units
V_{ISO}	Input-Output Isolation Voltage	$f = 60\text{Hz}$, $t = 1 \text{ sec.}$	7500			Vac(pk)
R_{ISO}	Isolation Resistance	$V_{I-O} = 500 \text{ VDC}$	10^{11}			Ω
C_{ISO}	Isolation Capacitance			0.2	2	pF

*All typicals at $T_A = 25^\circ\text{C}$

Electrical Characteristics (Continued) ($T_A = 25^\circ\text{C}$ unless otherwise specified)**Transfer Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Typ.*	Max.	Unit
DC CHARACTERISTICS							
CTR	Output Collector Current	$T_A = 0^\circ\text{C} - 70^\circ\text{C}$	MCT210M	150			%
		$I_F = 10\text{mA}, V_{CE} = 10\text{V}$	MCT2M MCT2EM	20			
			MCT271M	45		90	
			MCT210M	50			
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_C = 2\text{mA}, I_F = 16\text{mA}$	MCT2M MCT2EM MCT271M			0.4	V
		$I_C = 16\text{mA}, I_F = 32\text{mA}, T_A = 0^\circ\text{C} - 70^\circ\text{C}$	MCT210M				
AC CHARACTERISTICS							
t_{on}	AC Characteristic Saturated Turn-on Time from 5V to 0.8V	$I_F = 15\text{mA}, V_{CC} = 5\text{V}, R_L = 2\text{k}\Omega, R_B = \text{Open (Fig. 11)}$	MCT2M MCT2EM		1.1		μs
		$I_F = 20\text{mA}, V_{CC} = 5\text{V}, R_L = 2\text{k}\Omega, R_B = 100\text{k}\Omega \text{ (Fig. 11)}$	MCT2M MCT2EM		1.3		
t_{off}	Saturated Turn-off Time from SAT to 2.0 V	$I_F = 15\text{mA}, V_{CC} = 5\text{V}, R_L = 2\text{k}\Omega, R_B = \text{Open (Fig. 11)}$	MCT2M MCT2EM		50		μs
		$I_F = 20\text{mA}, V_{CC} = 5\text{V}, R_L = 2\text{k}\Omega, R_B = 100\text{k}\Omega \text{ (Fig. 11)}$	MCT2M MCT2EM		20		
t_{on}	Turn-on Time	$I_F = 10\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	MCT2M MCT2EM		2		μs
t_{off}	Turn-off Time	$I_F = 10\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	MCT2M MCT2EM		2		μs
t_r	Rise Time	$I_F = 10\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	MCT2M MCT2EM		2		μs
t_f	Fall Time	$I_F = 10\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	MCT2M MCT2EM		1.5		μs
t_{on}	Saturated turn-on time	$I_F = 16\text{mA}, R_L = 1.9\text{k}\Omega, V_{CC} = 5\text{V (Fig. 11)}$	MCT271M		1.0		μs
t_{off}	Saturated turn-off time (Approximates a typical TTL interface)				48		μs
t_{on}	Saturated turn-on time	$I_F = 16\text{mA}, R_L = 4.7\text{k}\Omega, V_{CC} = 5\text{V (Fig. 20)}$	MCT271M		1.0		μs
t_{off}	Saturated turn-off time (Approximates a typical low power TTL interface)				98		μs
t_r	Saturated rise time	$I_F = 16\text{mA}, R_L = 560\Omega, V_{CC} = 5\text{V (Fig. 11, 12)}$	MCT210M		1.0		μs
t_f	Saturated fall time				11		μs
$T_{PD(HL)}$	Saturated propagation delay – HIGH to LOW	$I_F = 16\text{mA}, R_L = 2.7\text{k}\Omega \text{ (Fig. 11, 12)}$	MCT210M		1.0		μs
$T_{PD(LH)}$	Saturated propagation delay – LOW to HIGH				50		μs
t_r	Non-saturated rise time	$I_C = 2\text{mA}, V_{CC} = 5\text{V}, R_L = 100\Omega \text{ (Fig. 11)}$	MCT210M		2		μs
t_f	Non-saturated fall time				2		μs
t_{on}	Non-saturated turn-on time	$I_C = 2\text{mA}, V_{CC} = 5\text{V}, R_L = 100\Omega \text{ (Fig. 20)}$	MCT271M		2	7	μs
t_{off}	Non-saturated turn-off time				2	7	μs

*All typicals at $T_A = 25^\circ\text{C}$

Safety and Insulation Ratings

As per IEC 60747-5-2, this optocoupler is suitable for “safe electrical insulation” only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Typ.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Main Voltage < 150Vrms		I-IV		
	For Rated Main voltage < 300Vrms		I-IV		
	Climatic Classification		55/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V_{PR}	Input to Output Test Voltage, Method b, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ sec, Partial Discharge < 5pC	1594			V_{peak}
	Input to Output Test Voltage, Method a, $V_{IORM} \times 1.5 = V_{PR}$, Type and Sample Test with $t_m = 60$ sec, Partial Discharge < 5pC	1275			V_{peak}
V_{IORM}	Max. Working Insulation Voltage	850			V_{peak}
V_{IOTM}	Highest Allowable Over Voltage	6000			V_{peak}
	External Creepage	7			mm
	External Clearance	7			mm
	Insulation Thickness	0.5			mm
RIO	Insulation Resistance at T_s , $V_{IO} = 500V$	10^9			Ω

Typical Performance Curves

Fig. 1 LED Forward Voltage vs. Forward Current

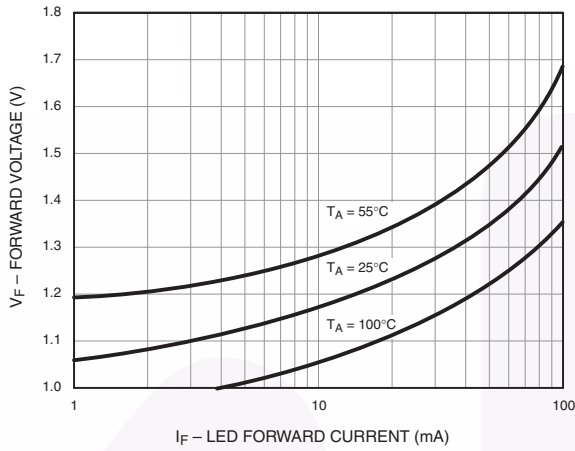


Fig. 2 Normalized CTR vs. Forward Current

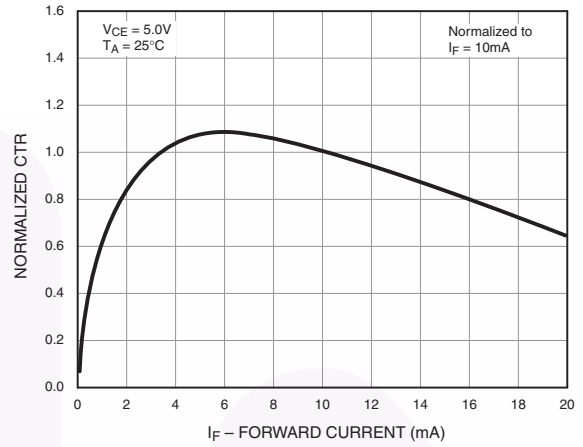


Fig. 3 Normalized CTR vs. Ambient Temperature

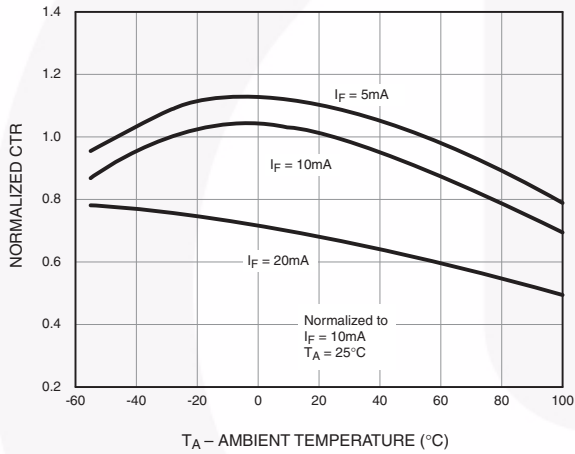


Fig. 4 CTR vs. RBE (Unsaturated)

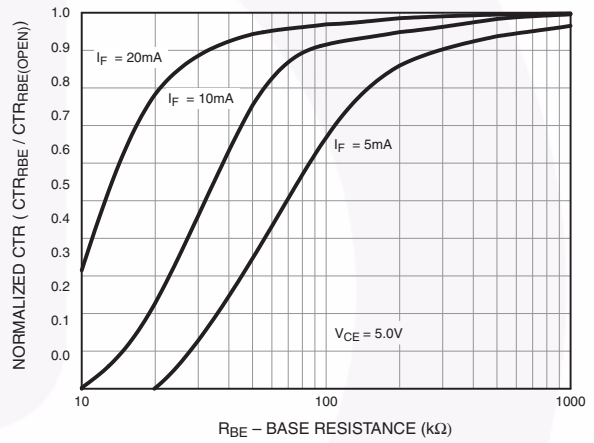


Fig. 5 CTR vs. RBE (Saturated)

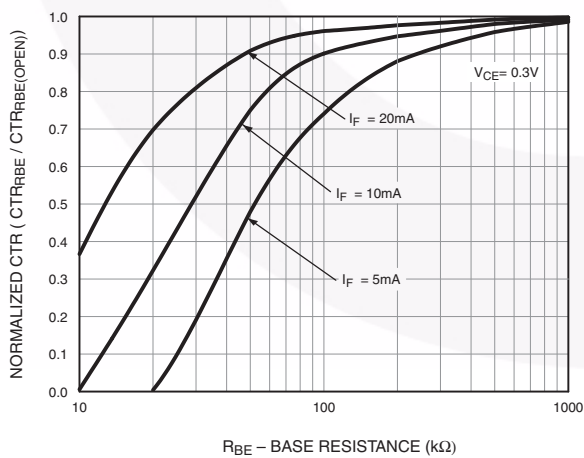
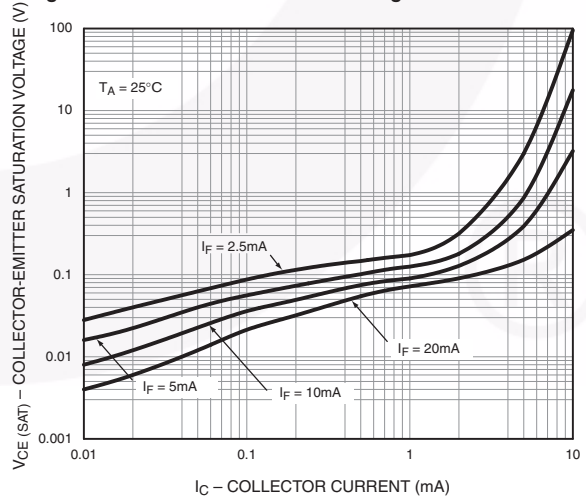


Fig. 6 Collector-Emitter Saturation Voltage vs Collector Current



Typical Performance Curves (Continued)

Fig. 7 Switching Speed vs. Load Resistor

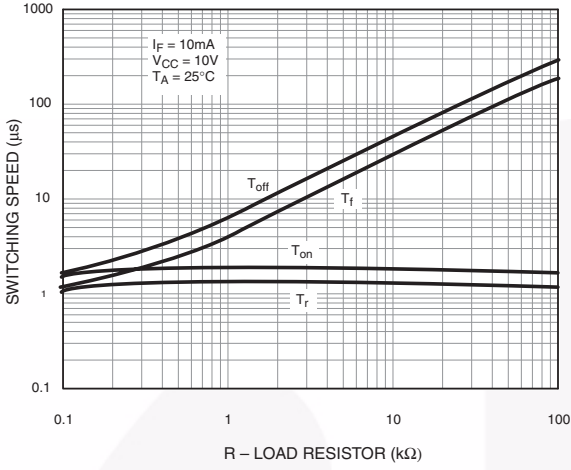


Fig. 8 Normalized t_{on} vs. R_{BE}

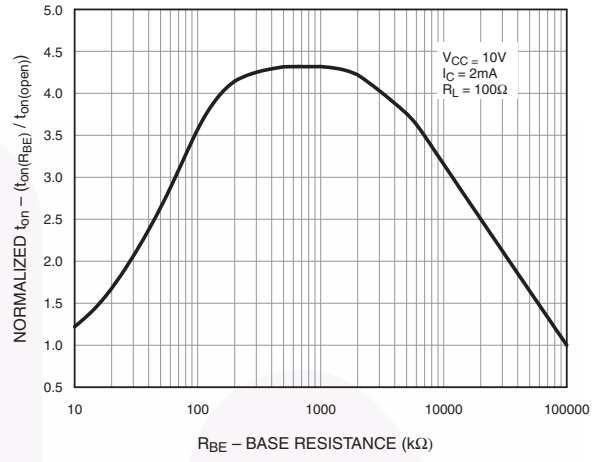


Fig. 9 Normalized t_{off} vs. R_{BE}

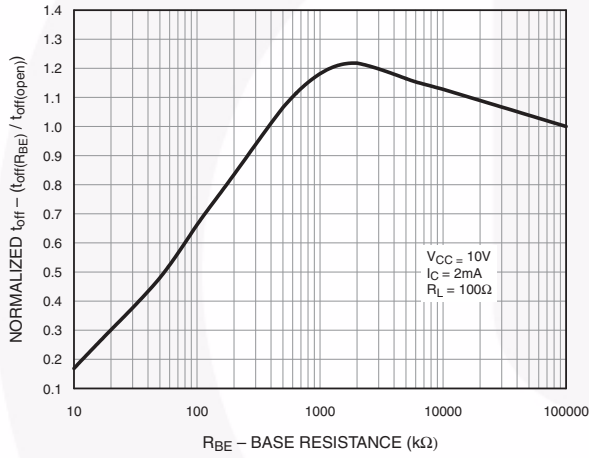
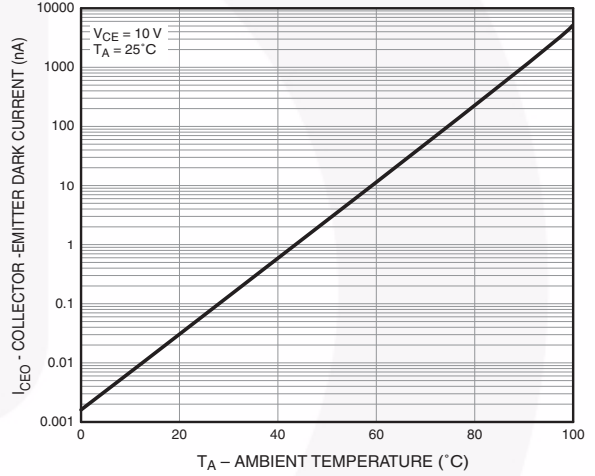


Fig. 10 Dark Current vs. Ambient Temperature



Typical Electro-Optical Characteristics

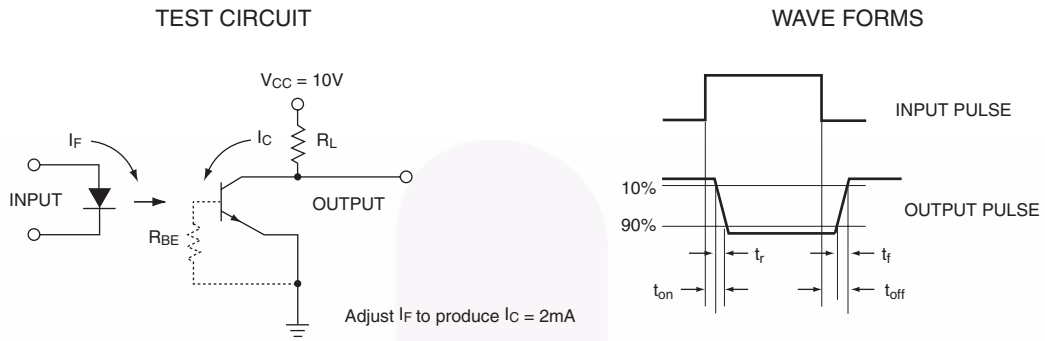


Figure 11. Switching Time Test Circuit and Waveforms

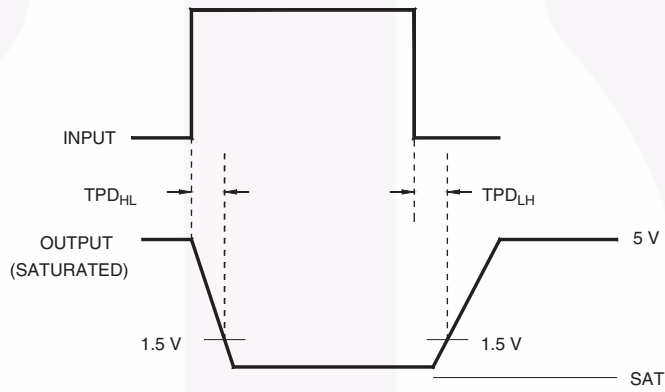
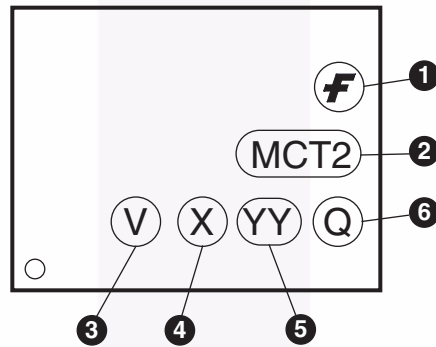


Figure 12. Switching Time Waveforms (MCT210M)

Ordering Information

Option	Order Entry Identifier (Example)	Description
No suffix	MCT2M	Standard Through Hole Device (50 units per tube)
S	MCT2SM	Surface Mount Lead Bend
SR2	MCT2SR2M	Surface Mount; Tape and Reel (1,000 units per reel)
T	MCT2TM	0.4" Lead Spacing
V	MCT2VM	IEC60747-5-2
TV	MCT2TVM	IEC60747-5-2, 0.4" Lead Spacing
SV	MCT2SVM	IEC60747-5-2, Surface Mount
SR2V	MCT2SR2VM	IEC60747-5-2, Surface Mount, Tape and Reel (1,000 units per reel)

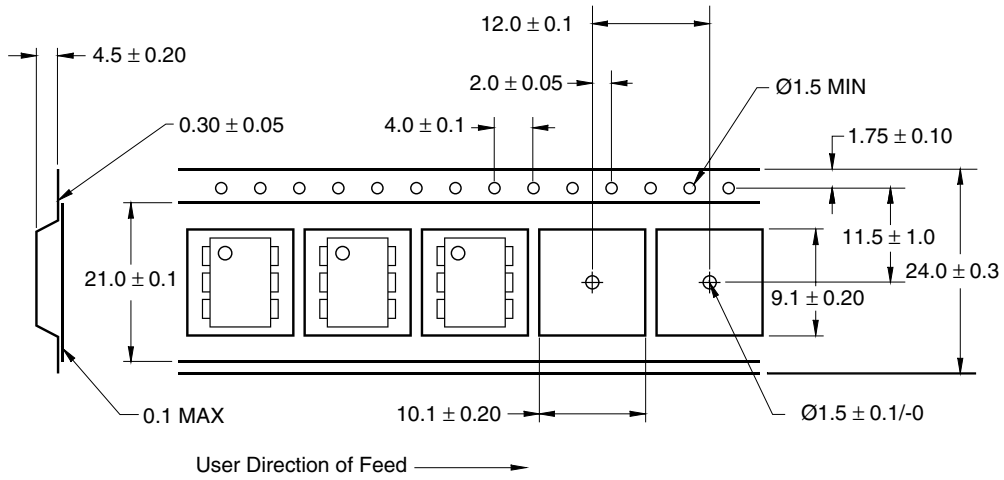
Marking Information



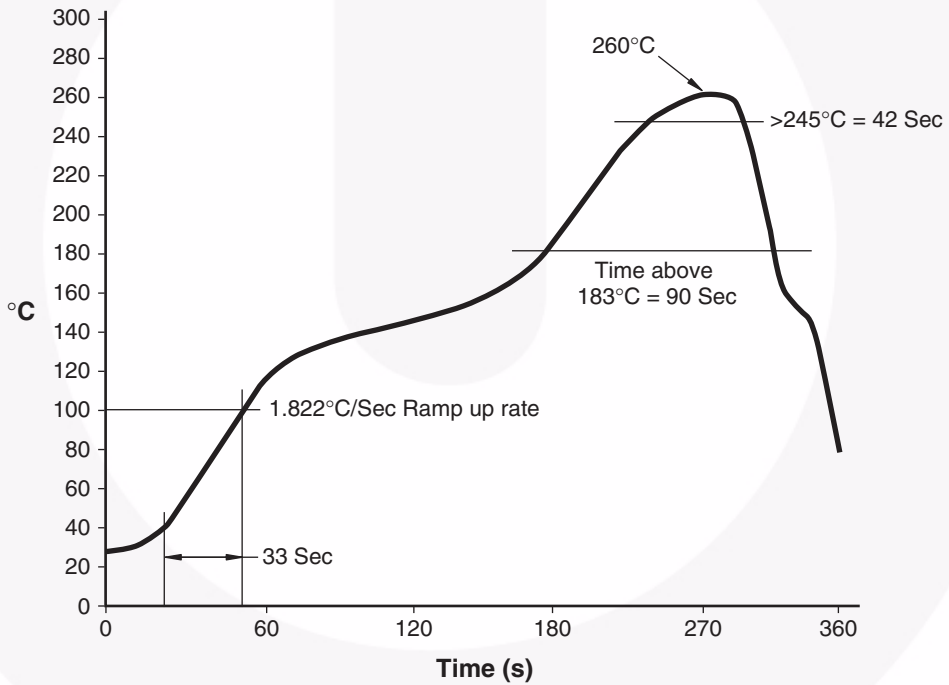
Definitions	
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '7'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.

Carrier Tape Specification



Reflow Profile





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